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TITLE: FORMATION OF WIRING PATTERN

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ABSTRACT:

PURPOSE: To remove the ruggedness of the upper insulating film by tapering the thick wiring sections by a method wherein etching process is performed using resist patterns covered with an intermediate layer resin as masks and after removing the intermediate resin, next etching process is performed using the other resist patterns as masks.

CONSTITUTION: An insulating film 2 comprising a thermal oxide film, an Al wiring 3, a lower layer resist 4 and an intermediate layer resin 5 are formed on an Si substrate 1. Next, upper layer resist patterns(RP) 6 are formed on the intermediate resin 5 and then interlayer resist patterns 5 are formed by etching process using the said upper layer patterns 6 as masks. After removing

the upper layer RPs 6, the lower layer RPs 4 re formed by etching process using the said intermediate layer resin patterns 5 as masks. Next, the Al film 3 is isotropically etched away halfway in the film thickness using the patterns 5 and the RPs 6 as masks so as to form tapers on the section of the film 3. Finally, the patterns 5 are removed and then the film 3 is etched away to make the sections vertical.

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